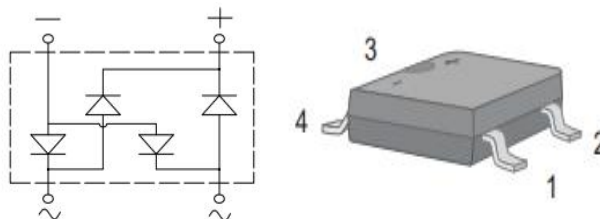


Bridge Rectifier Diode 整流桥

■ **Features 特点**

Glass passivated chip junction 玻璃钝化结
High surge current capability 高浪涌电流能力
Reflow Solder Temperature 220°C 回流焊温度 220 度
Package 封装: MBF



■ **Maximum Rating 最大额定值**

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	MB12F	MB14F	MB16F	MB18F	MB110F	MB115F	MB120F	Unit 单位
Peak Reverse Voltage 反向峰值电压	V_{RRM}	20	40	60	80	100	150	200	V
DC Reverse Voltage 直流反向电压	$V_{R(DC)}$	20	40	60	80	100	150	200	V
RMS Reverse Voltage 反向电压均方根值	$V_{R(RMS)}$	14	28	42	56	70	105	140	V
Forward Rectified Current 正向整流电流	I_F	1							A
Peak Surge Current 峰值浪涌电流	I_{FSM}	30							A
Thermal Resistance J-A 结到环境热阻	$R_{\theta JA}$	100							$^{\circ}\text{C}/\text{W}$
Junction Temperature 结温	T_J	150							$^{\circ}\text{C}$
Storage Temperature 储藏温度	T_{stg}	-55to+150 $^{\circ}\text{C}$							

■ **Electrical Characteristics 电特性**

($T_A=25^{\circ}\text{C}$ unless otherwise noted 如无特殊说明, 温度为 25°C)

Characteristic 特性参数	Symbol 符号	MB12F- MB14F	MB16F	MB18F- MB110F	MB115F- MB120F	Unit 单位	Condition 测试条件
Forward Voltage 正向电压降	V_F	0.55	0.7	0.85	0.9	V	$I_F=1\text{A}$
Reverse Current ($T_A=25^{\circ}\text{C}$) 反向漏电流($T_A=125^{\circ}\text{C}$)	I_R	300 10000		200 5000	100 2000	μA	$V_R=V_{RRM}$
Diode Capacitance 二极管电容	C_D	13				pF	$V_R=4\text{V}$, $f=1\text{MHz}$

■ Typical Characteristic Curve 典型特性曲线

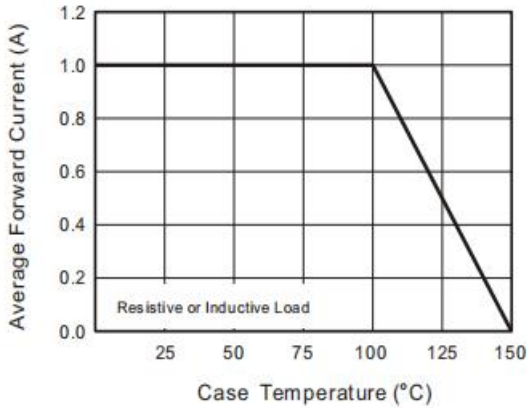


Figure 1: Forward Current Derating Curve

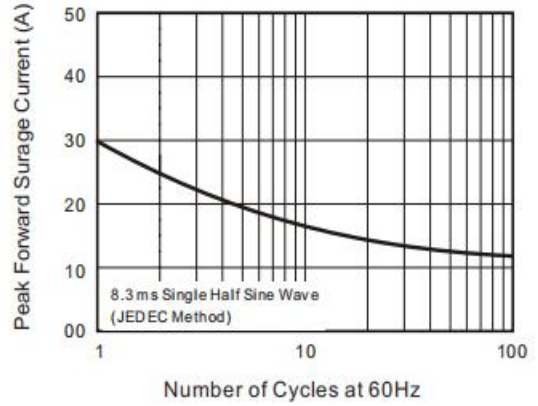


Figure 2: Peak Forward Surge Current

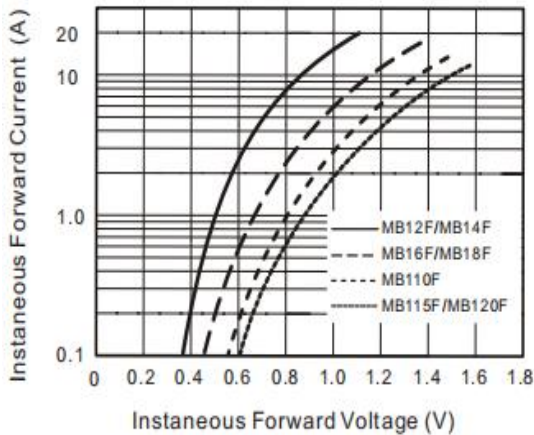


Figure 3: Instantaneous Forward Characteristics

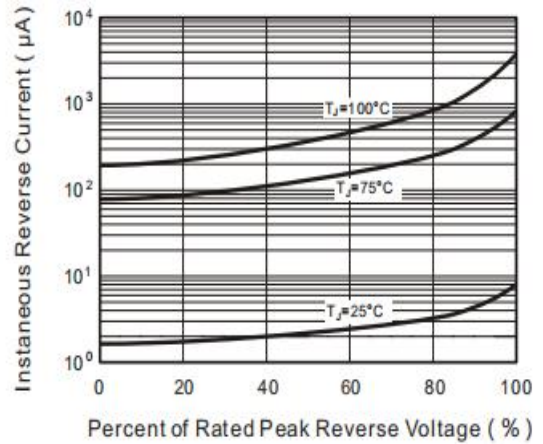


Figure 4: Reverse Leakage Characteristics

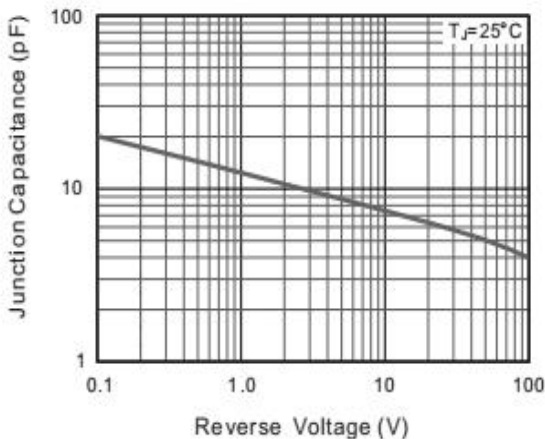


Figure 5: Junction Capacitance Characteristics

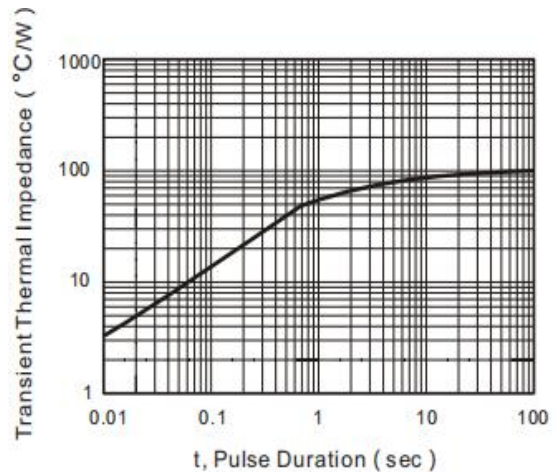
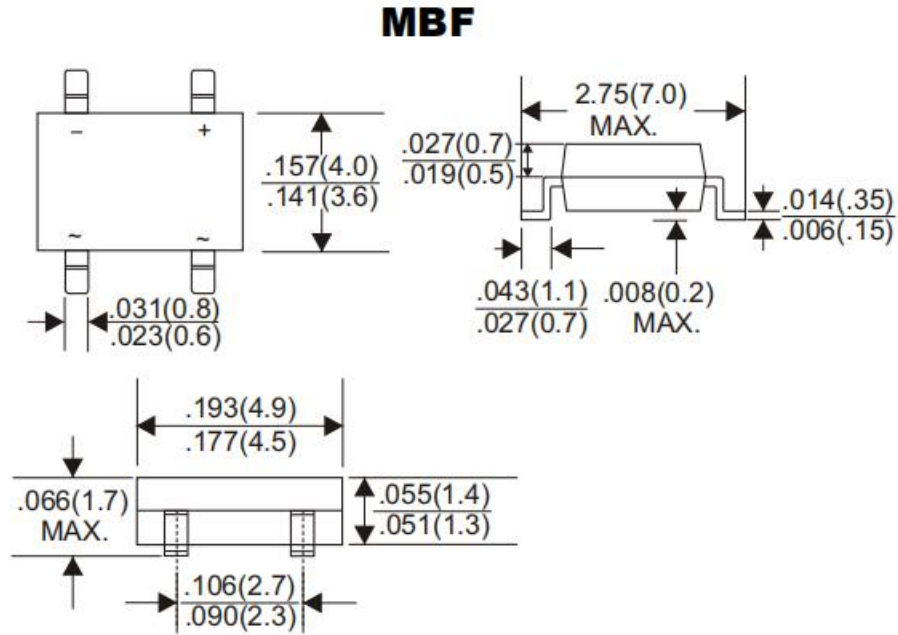


Figure 6: Transient Thermal Impedance

■Dimension 外形封装尺寸



Dimensions in inches and (millimeters)